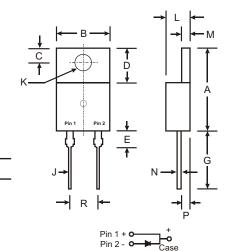


# MBR1030 - MBR1060

## **10A SCHOTTKY BARRIER RECTIFIER**

### **Features**

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Application
- Plastic Material: UL Flammability Classification Rating 94V-0



#### **TO-220AC** Dim Min Max Α 14.22 15.88 В 9.65 10.67 С 2.54 3.43 D 5.84 6.86 Е 6.35 G 12.70 14.73 0.51 1.14 J Κ 3.53Ø 4.09Ø L 3.56 4.83 M 1.14 1.40 0.30 0.64 Ν Р 2.03 2.92 R 4.83 5.33 All Dimensions in mm

### **Mechanical Data**

Case: Molded Plastic

 Terminals: Plated Leads Solderable per MIL-STD-202, Method 208

Polarity: See Diagram

Weight: 2.24 grams (approx.)

Mounting Position: AnyMarking: Type Number

### Maximum Ratings and Electrical Characteristics @ TA = 25°C unless otherwise specified

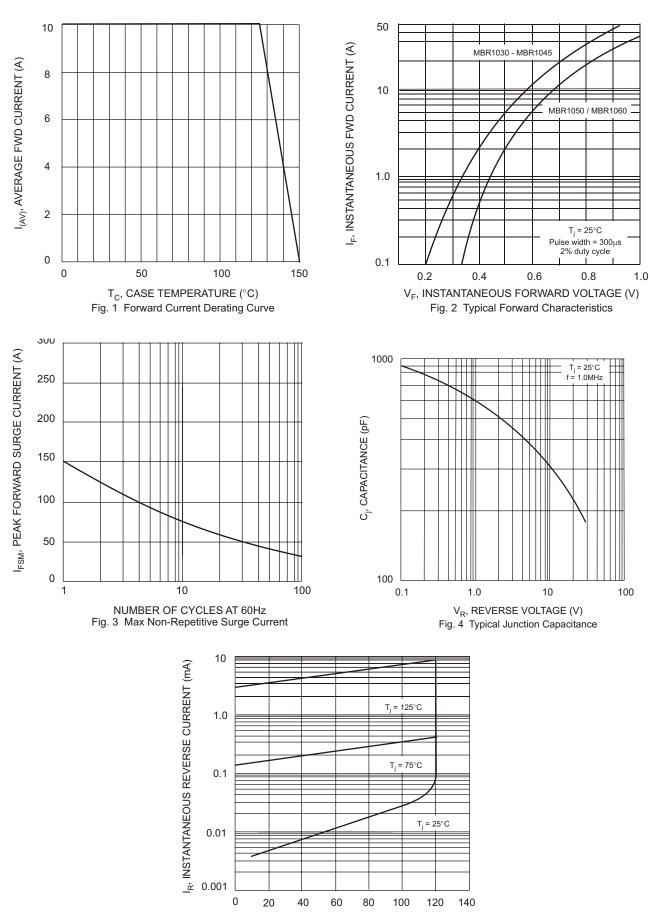
Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	MBR 1030	MBR 1035	MBR 1040	MBR 1045	MBR 1050	MBR 1060	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	30	35	40	45	50	60	V
RMS Reverse Voltage	V <sub>R(RMS)</sub>	21	24.5	28	31.5	35	42	V
Average Rectified Output Current (Note 1) @T <sub>C</sub> = 125°C	Io	10						А
Non-Repetitive Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	150						А
Forward Voltage Drop $@I_F = 10A, T_C = 25^{\circ}C$ $@I_F = 10A, T_C = 125^{\circ}C$		0.84 0.57					95 70	V
Peak Reverse Current $@T_C = 25^{\circ}C$ at Rated DC Blocking Voltage $@T_C = 125^{\circ}C$		0.1 15			0.1 25		mA	
Typical Junction Capacitance (Note 2)	Cj	400						pF
Typical Thermal Resistance Junction to Case (Note 1)	R <sub>θ</sub> Jc	2.5					°C/W	
Voltage Rate of Change (Rated V <sub>R</sub> )	dV/dt	1000					V/μs	
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-65 to +150						°C

Notes: 1. Thermal resistance junction to case mounted on heatsink.

2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.





PERCENT OF RATED PEAK REVERSE VOLTAGE (%) Fig. 5 Typical Reverse Characteristics